



ABSTRACT

Sub
A25

The present invention comprises a plurality of dies formed on the wafer and an I/O metal pad formed on the first surface of the wafer. Then, photo PI is coated on the first surface, then a portion of the PI is removed by laser. Next step, a first photoresist is coated on the second surface of the wafer and the photoresist includes positive photoresist. A first conductive layer is formed in the hole of the photo PI and covers a metal pad. Subsequently, a seeding layer with copper is formed on the top of the first conductive layer and the photo sensitive polymer layer. Then, a second photoresist is formed on the seeding layer to define the circuit pattern diagram. Then, a second conductive layer is formed. Next step is to remove the second and the first photoresist covered by the second photoresist, thereby forming trenches therein. Then, the filling material is filled into the trench and covers the circuit pattern diagram. A grinding process is performed to grind the second surface of the wafer to expose the filling material. Next step is to expose a portion of the circuit pattern to define an area formed by the conductive convex block. A solder screen printing step is used to form a solder on the defined area. The solder is re-flowed to form conductive bump.

10029764-040102